

Phase Control Thyristors (Hockey PUK Version), 960 A



E-PUK (TO-200AB)

PRIMARY CHARACTERISTICS					
I _{T(AV)}	960 A				
V _{DRM} /V _{RRM}	400 V, 600 V				
V_{TM}	1.60 V				
I _{GT}	100 mA				
T_J	-40 °C to +125 °C				
Package	E-PUK (TO-200AB)				
Circuit configuration	Single SCR				

FEATURES

- · Center amplifying gate
- Metal case with ceramic insulator
- International standard case E-PUK (TO-200AB)



- Low profile hockey PUK to increase current-carrying capability
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- · DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
		960	А			
I _{T(AV)}	T _{hs}	55	°C			
1		1900	Α			
I _{T(RMS)}	T _{hs}	25	°C			
1	50 Hz	15 000	٨			
ITSM	60 Hz	15 700	Α			
l ² t	50 Hz	1130	kA ² s			
1 - 1	60 Hz	1030	KA-S			
V _{DRM} /V _{RRM}		400 to 600	V			
tq	Typical	100	μs			
T _J		-40 to 125	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$\begin{aligned} I_{DRM}/I_{RRM}MAXIMUM\\ ATT_J = T_J\\ MAXIMUMmA \end{aligned}$				
VS-ST380CC	04	400 500		50				
VS-S1360CC 06		600	700	30				



ABSOLUTE MAXIMUM RATINGS	5				1	,
PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current	L	180° condu	180° conduction, half sine wave			Α
at heatsink temperature	I _{T(AV)}	double side	double side (single side) cooled			°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink tempe	erature double side cooled	1900	
		t = 10 ms	No voltage		15 000	A kA ² s
Maximum peak, one-cycle		t = 8.3 ms	reapplied		15 700	
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}	Sinusoidal half wave, initial $T_J = T_J$ maximum	12 600	
		t = 8.3 ms	reapplied		13 200	
Maximum I ² t for fusing		t = 10 ms No volt	No voltage reapplied		1130	
	l ² t	t = 8.3 ms			1030	
		t = 10 ms			800	
		t = 8.3 ms	reapplied		725	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10	t = 0.1 to 10 ms, no voltage reapplied			kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.85	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			V
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum			mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.24	1115.2
Maximum on-state voltage	V_{TM}	$I_{pk} = 3000 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			1.60	٧
Maximum holding current	I _H	T 05 00	T 0500 1 140V 111 1			m 1
Typical latching current	ΙL	T _J = 25 °C, anode supply 12 V resistive load			1000	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dI/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/μs
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1 A/\mu s$ $V_d = 0.67 \% V_{DRM}, T_J = 25 °C$	1.0	
Typical turn-off time	t _q	I_{TM} = 550 A, T_J = T_J maximum, dl/dt = 40 A/ μ s, V_R = 50 V, dV/dt = 20 V/ μ s, gate 0 V 100 Ω , t_p = 500 μ s	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM,} I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	50	mA



TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES		UNITS
PARAMETER	STINIBUL	IES	SI CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	10.0		w
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	VV
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms	3	.0	Α
Maximum peak positive gate voltage	+ V _{GM}	T T manyimum i	t < E ma	20		V
Maximum peak negative gate voltage	- V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms			.0] '
		T _J = -40 °C	Maximum required gate trigger/	200	-	
DC gate current required to trigger	I _{GT}	T _J = 25 °C		100	200	mA
	T _J = 125 °C current/voltage are the lowest		50	-		
		T _J = -40 °C	value which will trigger all units		-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	12 V anode to cathode applied	1.8	3.0	٧
	T _J = 125 °C			1.1	-	
DC gate current not to trigger	I _{GD}	T T manyimay	Maximum gate current/voltage not to trigger is the maximum	10		mA
DC gate voltage not to trigger	V_{GD}	T _J = T _J maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied		0.	25	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	YMBOL TEST CONDITIONS		UNITS	
Maximum operating junction temperature range	T_{J}		-40 to 125	- °C	
Maximum storage temperature range	T _{Stg}		-40 to 150	C	
Maximum thermal resistance, junction to heatsink	D	DC operation single side cooled	0.09		
	R _{thJ-hs}	DC operation double side cooled	0.04	K/W	
Maximum thermal resistance, case to heatsink	R _{thC-hs}	DC operation single side cooled	cooled 0.02		
Maximum thermal resistance, case to heatslink		DC operation double side cooled	0.01		
Mounting force, ± 10 %			9800 (1000)	N (kg)	
Approximate weight			83	g	
Case style		See dimensions - link at the end of datasheet	E-PUK (TO-2	200AB)	

△R _{thJ-hs} CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEGT COMPITIONS	LINITE	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS	
180°	0.010	0.011	0.007	0.007			
120°	0.012	0.012	0.012	0.013	T _J = T _J maximum		
90°	0.015	0.015	0.016	0.017		K/W	
60°	0.022	0.022	0.023	0.023			
30°	0.036	0.036	0.036	0.037			

Note

• The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

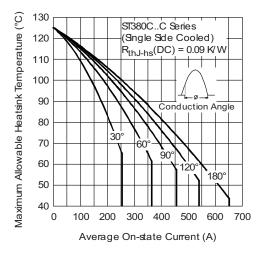


Fig. 1 - Current Ratings Characteristics

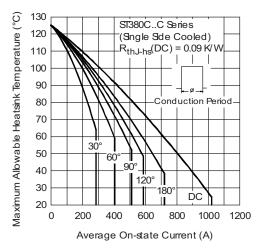


Fig. 2 - Current Ratings Characteristics

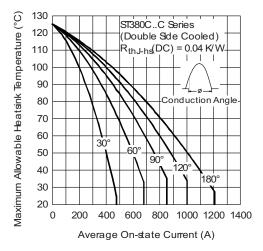


Fig. 3 - Current Ratings Characteristics

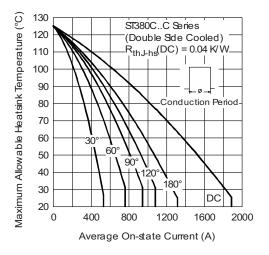


Fig. 4 - Current Ratings Characteristics

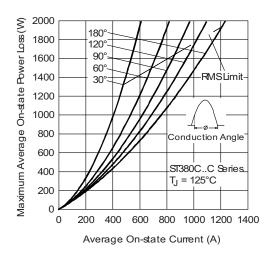


Fig. 5 - On-State Power Loss Characteristics

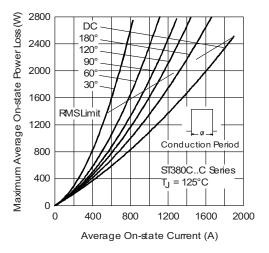


Fig. 6 - On-State Power Loss Characteristics

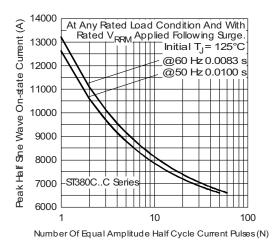


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

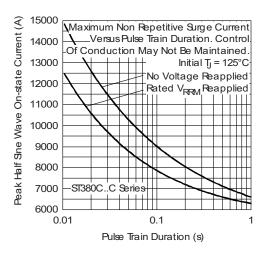


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

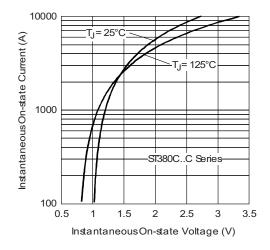


Fig. 9 - On-State Voltage Drop Characteristics

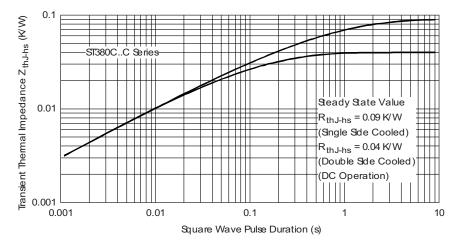


Fig. 10 - Thermal Impedance $Z_{thJ\text{-}hs}$ Characteristics

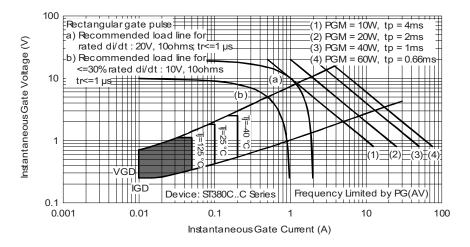
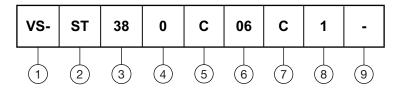


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Thyristor

3 - Essential part number

4 - 0 = converter grade

5 - C = ceramic PUK

6 - Voltage code x 100 = V_{RRM} (see Voltage Ratings table)

7 - C = PUK case E-PUK (TO-200AB)

- 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads)

1 = fast-on terminals (gate and auxiliary cathode unsoldered leads)

2 = eyelet terminals (gate and auxiliary cathode soldered leads)

3 = fast-on terminals (gate and auxiliary cathode soldered leads)

9 - Critical dV/dt: • None = 500 V/µs (standard selection)

• L = 1000 V/µs (special selection)

LINKS TO RELATED DOCUMENTS				
Dimensions	http://www.vishay.com/doc?95075			

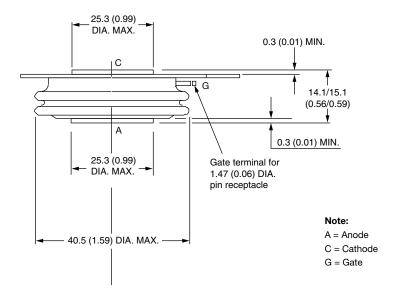


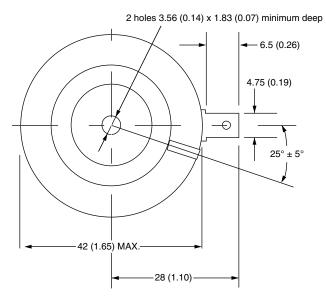
E-PUK (TO-200AB)

DIMENSIONS in millimeters (inches)

Anode to gate

Creepage distance: 11.18 (0.44) minimum Strike distance: 7.62 (0.30) minimum





Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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